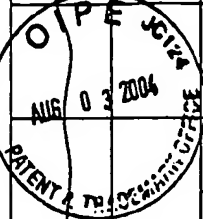

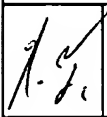
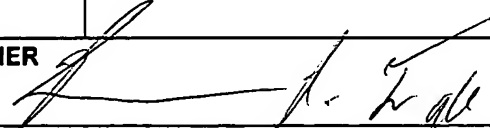


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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				APPLICANT Luke J. Mawst, et al.				
				FILING DATE 02/05/2004		GROUP ART UNIT 2811		
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							YES	NO
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EXAMINER		DATE CONSIDERED 9/18/05
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		I. Vurgaftman and J.R. Meyer, "(In) GaAsN-based type-II 'W' quantum-well lasers for emission at $\lambda=1.55\mu\text{m}$," Appl. Phys. Lett., Vol. 83, No. 14, 6 October 2003, pp. 2742-2744.					
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Submitted: January 20, 2005

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APPLICANT

Luke J. Mawst, et al.

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2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
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							YES	NO

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